

## Diode, Wechselrichter / Diode, Inverter

### Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	650	V
Dauergleichstrom Continuous DC forward current		$I_F$	30	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_P = 1\text{ ms}$	$I_{FRM}$	60	A
Grenzlastintegral $I^2t$ - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	$I^2t$	90,0 82,0	$\text{A}^2\text{s}$ $\text{A}^2\text{s}$

### Charakteristische Werte / Characteristic Values

		min. typ. max.				
Durchlassspannung Forward voltage	$I_F = 30\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		1,60	2,00	V
	$I_F = 30\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$	$V_F$	1,55		V
	$I_F = 30\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		1,50		V
Rückstromspitze Peak reverse recovery current	$I_F = 30\text{ A}, -di_F/dt = 1100\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$	$T_{vj} = 25^{\circ}\text{C}$	$I_{RM}$	20,0		A
	$V_R = 300\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$		26,0		A
	$V_{GE} = -15\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		28,0		A
Sperrverzögerungsladung Recovered charge	$I_F = 30\text{ A}, -di_F/dt = 1100\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$	$T_{vj} = 25^{\circ}\text{C}$	$Q_r$	1,20		$\mu\text{C}$
	$V_R = 300\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$		2,10		$\mu\text{C}$
	$V_{GE} = -15\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		2,50		$\mu\text{C}$
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 30\text{ A}, -di_F/dt = 1100\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$	$T_{vj} = 25^{\circ}\text{C}$	$E_{rec}$	0,22		mJ
	$V_R = 300\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$		0,45		mJ
	$V_{GE} = -15\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		0,53		mJ
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro Diode / per diode	$R_{thJH}$		2,60		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions		$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

## IGBT,3-Level / IGBT,3-Level

### Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{CES}$	650	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_H = 25^{\circ}\text{C}, T_{vj\text{ max}} = 175^{\circ}\text{C}$	$I_{C\text{ nom}}$	30	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	$I_{CRM}$	60	A
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		$V_{GES}$	+/-20	V

### Charakteristische Werte / Characteristic Values

			min.	typ.	max.		
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 30\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 30\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 30\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	1,55 1,80 1,85	1,95	V V V	
Gate-Schwellenspannung Gate threshold voltage	$I_C = 0,80\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{GEth}$	5,00	5,80	6,50	V
Gateladung Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		$Q_G$	0,30			$\mu\text{C}$
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{Gint}$	0,0			$\Omega$
Eingangskapazität Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{ies}$	1,65			nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{res}$	0,051			nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 650\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{CES}$			1,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{GES}$			100	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 30\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 20\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{don}$	0,03 0,03 0,031			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 30\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 20\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_r$	0,035 0,036 0,05			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 30\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 20\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{doff}$	0,175 0,19 0,20			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
Fallzeit, induktive Last Fall time, inductive load	$I_C = 30\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 20\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_f$	0,019 0,038 0,043			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 30\text{ A}, V_{CE} = 300\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 830\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 20\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{on}$	0,38 0,42 0,42			mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 30\text{ A}, V_{CE} = 300\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 5400\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 20\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{off}$	0,42 0,64 0,71			mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 360\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	$t_P \leq 5\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	$I_{SC}$	160			A
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro IGBT / per IGBT		$R_{thJH}$	2,15			K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150		$^{\circ}\text{C}$